



SSCP5401GSG

Dual PNP Switching Transistor

➤ Features

VCB	VCE	VEB	IC
-160V	-150V	-6V	-200mA

➤ Description

This device is designed for general-purpose high-voltage amplifiers and gas discharge display drivers. It is Ideal for medium power amplification and switching.

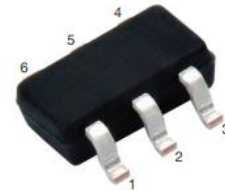
➤ Applications

- General-purpose high-voltage amplifiers
- Gas discharge display drivers
- Medium power amplification and switching

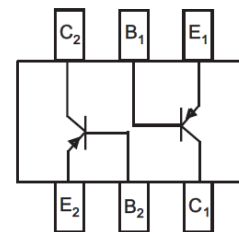
➤ Ordering Information

Device	Package	Shipping
SSCP5401GSG	SOT-363	3000/Reel

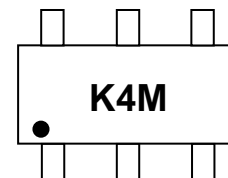
➤ Pin configuration



SOT-363



Circuit Diagram



Marking (Top View)



➤ **Absolute Maximum Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

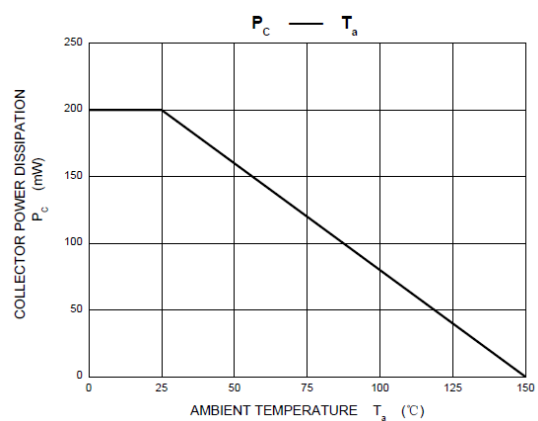
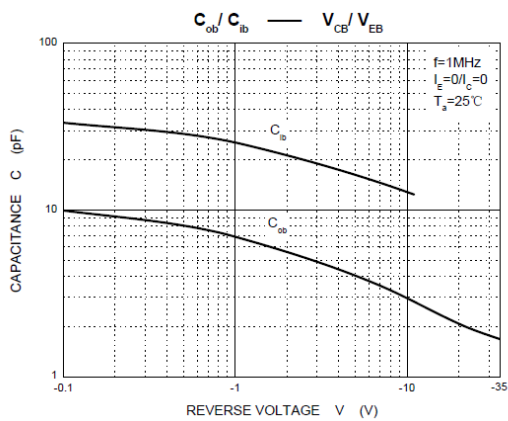
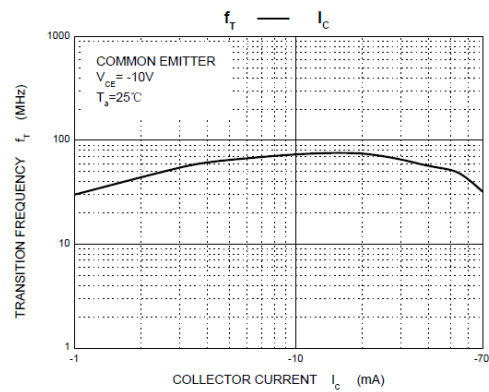
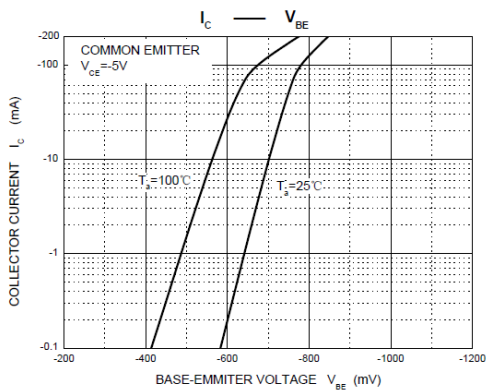
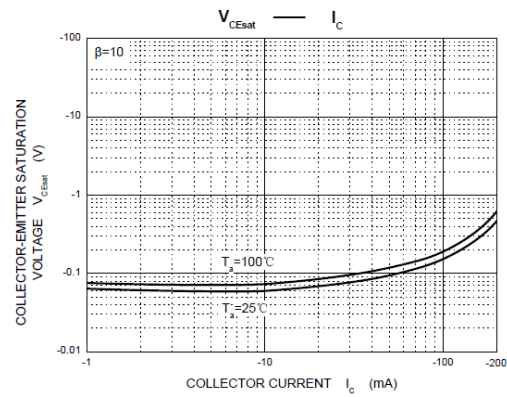
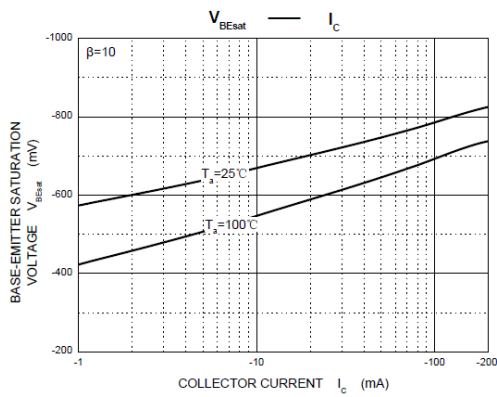
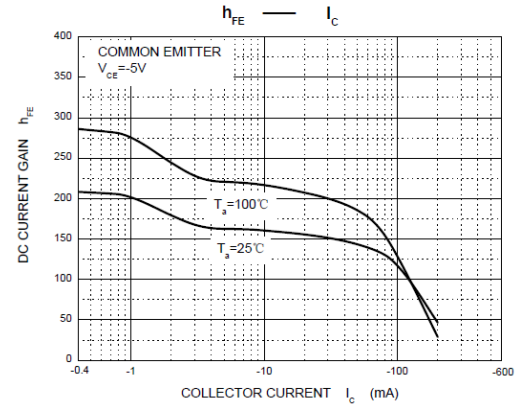
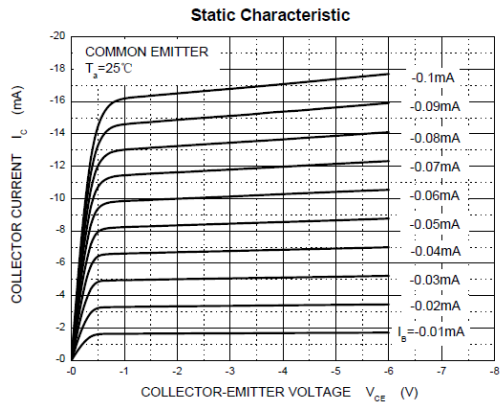
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	-160	V
Collector- Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current-Continuous	I_C	-200	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 to 150	$^{\circ}\text{C}$

➤ **Electrical Characteristics** ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	BV_{CB0}	$I_C=-100\mu\text{A}, I_E=0$	-160			V
Collector-emitter Breakdown Voltage	BV_{CEO}	$I_C=-1\text{mA}, I_B=0$	-150			V
Emitter -Base Breakdown Voltage	BV_{EBO}	$I_E=-100\mu\text{A}, I_C=0$	-5			V
Collector Cutoff Current	I_{CBO}	$V_{CB}=-120\text{V}, I_E=0$			-50	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-3\text{V}, I_C=0$			-50	nA
DC Current Gain	h_{FE}	$V_{CE}=-5\text{V}, I_C=-10\text{mA}$	100		300	
		$V_{CE}=-5\text{V}, I_C=-50\text{mA}$	50			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-1.0	V
Output Capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$			6	pF
Transition frequency	f_T	$V_{CE}=-10\text{V}, I_C=-10\text{mA}$ $f=100\text{MHz}$	100			MHz



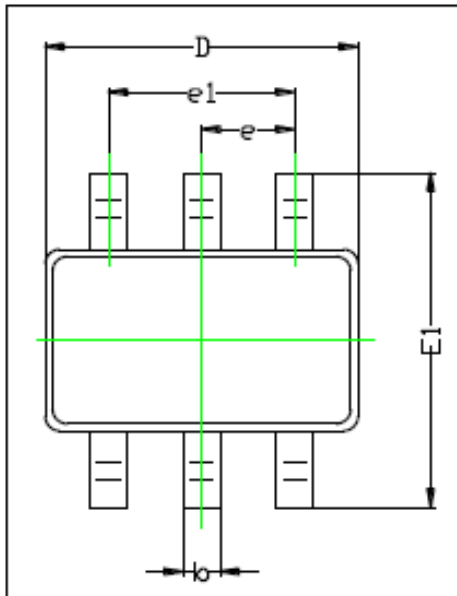
➤ Typical Performance Characteristics (TA=25°C unless otherwise noted)



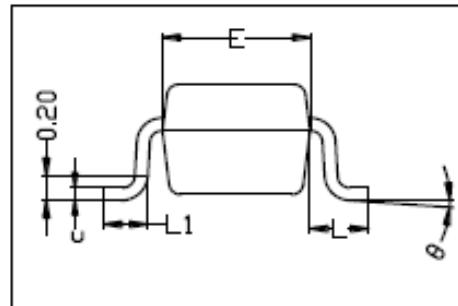
➤ Package Information

SOT-363

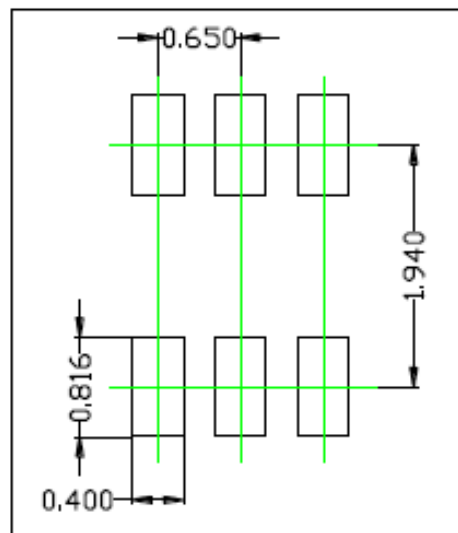
TOP VIEW



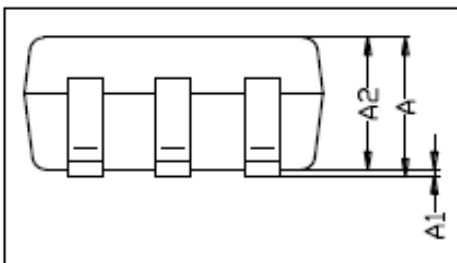
SIDE VIEW



SOLDING PATTERN



FRONT VIEW



SYMBOL	DIMENSIONS IN MILLIMETER	
	MIN	MAX
A	0.900	1.000
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.300
c	0.100	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.400
e	0.650 TYP.	
e1	1.200	1.400
L	0.525 REF.	
L1	0.260	0.450
θ	0°	8°



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